CHEMICAL VAPOUR DEPOSITION FROM A RADIATION-SENSITIVE PRECURSOR

The present invention relates in one aspect to a method of depositing a thin film on a substrate by chemical vapour deposition (CVD) from a radiation-sensitive precursor substance. The method comprises the steps of: (i) placing the substrate in a reaction chamber of a CVD system; (ii) heating the substrate, wherein heating includes the transmission of electromagnetic heating radiation from a controllable radiative heat source through the reaction chamber towards the substrate, wherein the radiative heat source is controlled to provide electromagnetic radiation as one or more heating pulses, each heating pulse followed by an idle period; (iii) during at least one of the idle periods, providing a pressure pulse of precursor substance inside the reaction chamber by feeding at least one precursor substance to the reaction chamber so as to establish a reaction partial pressure for thin film deposition from said pre-cursor substance onto the substrate and subsequently, after a dwell time, removing the precursor substance so as to reduce the partial pressure of the precursor substance in the reaction chamber to below a threshold; and (iv) repeating steps (ii) and (iii) until a desired thin film is formed. According to a further aspect, the invention relates to a chemical vapour deposition (CVD) system for depositing a thin film onto a substrate using precursor substances containing at least one radiation sensitive species.

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